

ISOPLUS i4-PAC™



Outline drawings on pages O-29...O-51

Type with MOSFET	Configu- ration	Circuit diagram / Technology	V_{CES} V	I_{CES} $T_C = 25^\circ\text{C}$ A	I_{CSO} $T_C = 90^\circ\text{C}$ A	$R_{DS(on)}$ typ. $T_C = 25^\circ\text{C}$ Ω	Fig. No.	Circuit Diagram
> New								
> IXTF 280N055T	single	A Trench MOSFET	55	160	*	0.004	X024d	
> IXTF 250N075T		A Trench MOSFET	75	140	*	0.0044		
> IXTF 230N085T		A Trench MOSFET	85	130	*	0.0053		
> IXTF 200N10T		A Trench MOSFET	100	90	*	0.007		
> IXFF 80N50Q2		A Q2-Class MOSFET	500	80	*	0.066	X024b X024a	
IXKF 40N60SCD1		G CoolMOS™ & serial Schottky & HiPerFRED free wheeling Diode	600	41	29	0.060		
> IXKF 40N60SCH1		G CoolMOS™ & serial Schottky & SONIC free wheeling Diode	600	41	29	0.060	X024c	
IXTF 1N250		A High Voltage MOSFET	2500	1	*	40		
IXTF 03N400		A High Voltage MOSFET	4000	0.3	*	300		
IXTF 1N400		A High Voltage MOSFET	4000	1	*	60		
FDM 15-06KC5	buck	E CoolMOS™ & HiPerDynFRED	600	15	11	0.15	X024a	
FDM 47-06KC5		E CoolMOS™ & HiPerDynFRED	600	47	32	0.04		
FMD 21-05QC	boost	E HiPerFET & HiPerDynFRED	500	21	15	0.18		
> MPA 22R600DHGFC		C POLAR™ & SONIC Diode	600	15	11	0.22		
> MKE 11R600DCGFC		C CoolMOS™ & SiC Diode	600	15	11	0.15		
FMD 15-06KC5		D CoolMOS™ & HiPerDynFRED	600	15	11	0.15		
FMD 40-06KC		D CoolMOS™ & HiPerDynFRED	600	38	25	0.06		
FMD 47-06KC5		D CoolMOS™ & HiPerDynFRED	600	47	32	0.04		
FMM 75-01F	phase leg	B HiPerFET	100	75	50	0.02		

* in progress

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Type with IGBT	Configu- ration	Circuit diagram / Technology	V_{CES} V	I_{CES} $T_C = 25^\circ\text{C}$ A	I_{CSO} $T_C = 90^\circ\text{C}$ A	$V_{CE(sat)}$ typ. $T_C = 25^\circ\text{C}$ V	Fig. No.	Circuit Diagram
> New								
IXBF 9N160G	single	I BiMOSFET	1600	7	4	4.9	X024c	
IXBF 40N160		I BiMOSFET	1600	28	16	6.2		
> IXGF 32N170		H High voltage IGBT	1700	44	*	2.7		
> IXGF 20N250		H High voltage IGBT	2500	23	14	max 3.1		
> IXGF 25N250		H High voltage IGBT	2500	30	*	max 2.9		
IXLF 19N250A		H High voltage IGBT	2500	32	*	max 3.9		
IXBF12N300		I BiMOSFET	3000	22	12	3.2		
IXBF 20N300		I BiMOSFET	3000	27	15	3.2		
IXGF 20N300		H High voltage IGBT	3000	*	*	3.2		
IXGF 25N300		H High voltage IGBT	3000	*	*	3.0		
IXBF 32N300		I BiMOSFET	3000	40	22	3.2		
IXGF 36N300		H High voltage IGBT	3000	*	*	2.7		
IXBF 55N300		I BiMOSFET	3000	73	*	3.2		
> IXGF30N400		H High voltage IGBT	4000	15	*	3.1		
FID 60-06D	boost	K NPT IGBT & HiPerFRED	600	65	40	1.6	X024a	
FII 30-06D	phase leg	J NPT IGBT	600	30	18	1.9		
FII 40-06D		J NPT IGBT	600	40	25	1.8		

* in progress

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Type Bipolar	Configuration	Circuit diagram / Diode type	Voltage V	$I_{D(AV)}$ $T_C = 90^\circ\text{C}$ A	Fig. No.	Circuit Diagram
> New						
> CNA 10E2500FB CS 20-22moF1 CS 20-25mo1F	single part, high voltage	R Thyristor R Thyristor R Thyristor	2500 2200 2500	10 18 18	X024c	
DSEE 55-24N1F	phase leg	L HiperFRED	2x 1200	55	X024b	
> CLA 40P1200FC		Q Thyristor	2x 1200	40	X024a	
CMA 30P1600FC		Q Thyristor	2x 1600	30		
CMA 50P1600FC		Q Thyristor	2x 1600	50		
DHH 55-36N1F		L Sonic-FRD	2x 1800	50	X024b	
FBS 10-06SC	1-phase bridge	M Si-Carbide	600	6.6	X024a	
FBS 16-06SC		M Si-Carbide	600	11		
FBE 22-06N1		N HiperFRED	600	20		
FBO 16-12N		N Rectifier	1200	22		
> FBS 10-12SC		M Si-Carbide	1200	10		
FBO 40-12N		N Rectifier	1200	40		
FUS 45-0045B	3-phase bridge	P Schottky	45	45		
FUE 30-12N1		O HiperFRED	1200	30		
FUO 22-12N		O Rectifier	1200	27		
FUO 22-16N		O Rectifier	1600	27		
FUO 50-16N		O Rectifier	1600	50		

